

Ethernet/10BaseT/100BaseT Protector



The DO-214AA *SIDACtor* Ethernet protection series is intended for applications sensitive to load values. Typically, high speed connections require a lower capacitance. C_0 values are 40% lower than standard devices.

SIDACtor devices are used to enable equipment to meet various regulatory requirements including GR 1089, ITU K.20, K.21 and K.45, IEC 60950, UL 60950, and TIA-968 (formerly known as FCC Part 68).

Electrical Parameters

Part Number *	V _{DRM} Volts	V _S Volts	V _T Volts	I _{DRM} μ Amps	I _S mAmps	I _T Amps	I _H mAmps	C ₀ pF
P0642S_	58	77	4	5	800	2.2	120	25
P0722S_	65	88	4	5	800	2.2	120	25
P0902S_	75	98	4	5	800	2.2	120	25
P1102S_	90	130	4	5	800	2.2	120	20
P3002S_	280	360	4	5	800	2.2	120	15

* For surge ratings, see table below.

General Notes:

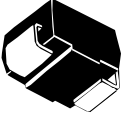
- All measurements are made at an ambient temperature of 25 °C. I_{PP} applies to -40 °C through +85 °C temperature range.
- I_{PP} is a repetitive surge rating and is guaranteed for the life of the product.
- Listed *SIDACtor* devices are bi-directional. All electrical parameters and surge ratings apply to forward and reverse polarities.
- V_{DRM} is measured at I_{DRM}.
- V_S is measured at 100 V/ μ s.
- Special voltage (V_S and V_{DRM}) and holding current (I_H) requirements are available upon request.
- Off-state capacitance is measured at 1 MHz with a 2 V bias.

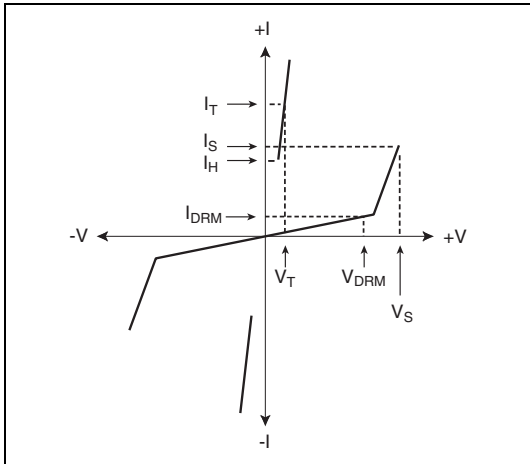
Surge Ratings

Series	I _{PP} 2x10 μ s Amps	I _{PP} 8x20 μ s Amps	I _{PP} 10x160 μ s Amps	I _{PP} 10x560 μ s Amps	I _{PP} 10x1000 μ s Amps	I _{TSM} 60 Hz Amps	di/dt Amps/ μ s
A	150	150	90	50	45	20	500
B**	250	250	150	100	80	30	500

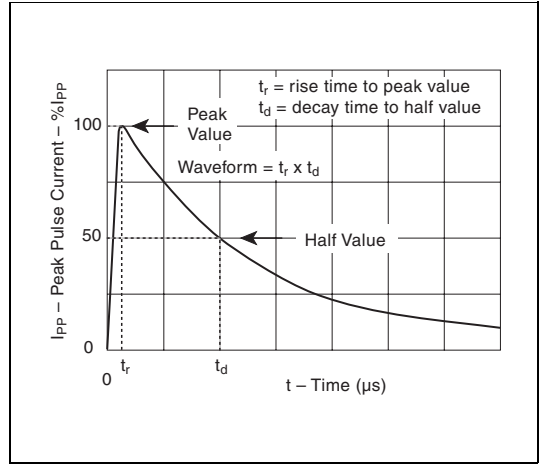
** Contact factory for release date of B-rated devices.

Thermal Considerations

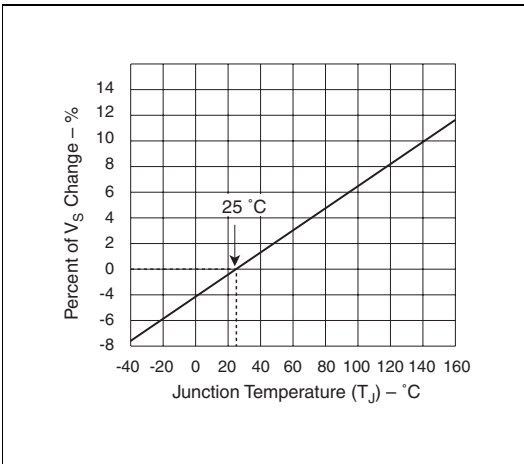
Package	Symbol	Parameter	Value	Unit
	T_J	Operating Junction Temperature Range	-40 to +150	$^{\circ}\text{C}$
	T_S	Storage Temperature Range	-65 to +150	$^{\circ}\text{C}$
	$R_{\theta JA}$	Thermal Resistance: Junction to Ambient	90	$^{\circ}\text{C}/\text{W}$



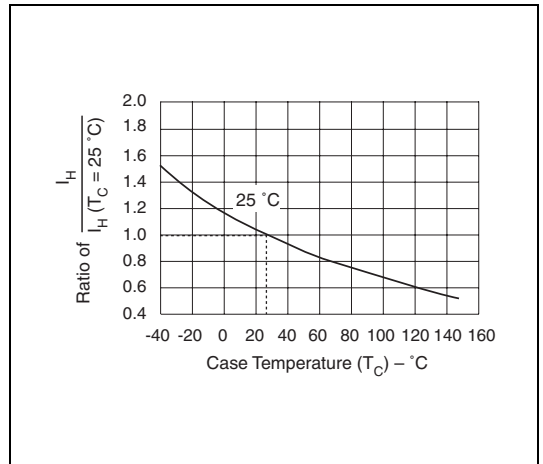
V-I Characteristics



$t_r \times t_d$ Pulse Wave-form



Normalized V_S Change versus Junction Temperature



Normalized DC Holding Current versus Case Temperature

Data Sheets